

MMBT2907AWT1G, NSVMMBT2907AWT1G

General Purpose Transistor

PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	-60	Vdc
Collector–Base Voltage	V_{CBO}	-60	Vdc
Emitter–Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

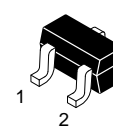
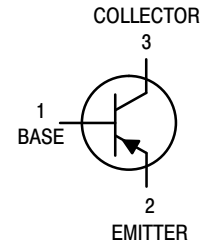
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



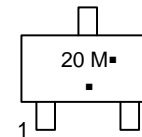
ON Semiconductor®

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SC-70/SOT-323
CASE 419-04
STYLE 3

MARKING DIAGRAM



20 = Specific Device Code
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel
NSVMMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 2) ($I_C = -10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-60	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -10\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	-60	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Base Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB(off)} = -0.5\text{ Vdc}$)	I_{BL}	-	-50	nAdc
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB(off)} = -0.5\text{ Vdc}$)	I_{CEX}	-	-50	nAdc

ON CHARACTERISTICS⁽³⁾

DC Current Gain (Note 2) ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -10\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -150\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -500\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$)	H_{FE}	75 100 100 100 50	- - - 340 -	-
Collector-Emitter Saturation Voltage (Note 2) ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{CE(sat)}$	- -	-0.4 -1.6	Vdc
Base-Emitter Saturation Voltage (Note 2) ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{BE(sat)}$	- -	-1.3 -2.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product ($I_C = -50\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	200	-	MHz
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	-	8.0	pF
Input Capacitance ($V_{EB} = -2.0\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	-	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = -30\text{ Vdc}$, $I_C = -150\text{ mAdc}$, $I_{B1} = -15\text{ mAdc}$)	t_{on}	-	45	ns
Delay Time		t_d	-	10	
Rise Time		t_r	-	40	
Storage Time	$(V_{CC} = -6.0\text{ Vdc}$, $I_C = -150\text{ mAdc}$, $I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_s	-	80	
Fall Time		t_f	-	30	
Turn-Off Time		t_{off}	-	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

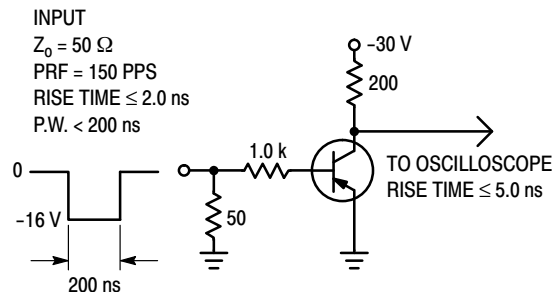


Figure 1. Delay and Rise Time Test Circuit

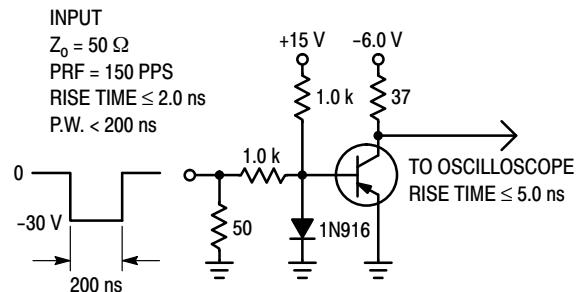


Figure 2. Storage and Fall Time Test Circuit

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TYPICAL CHARACTERISTICS

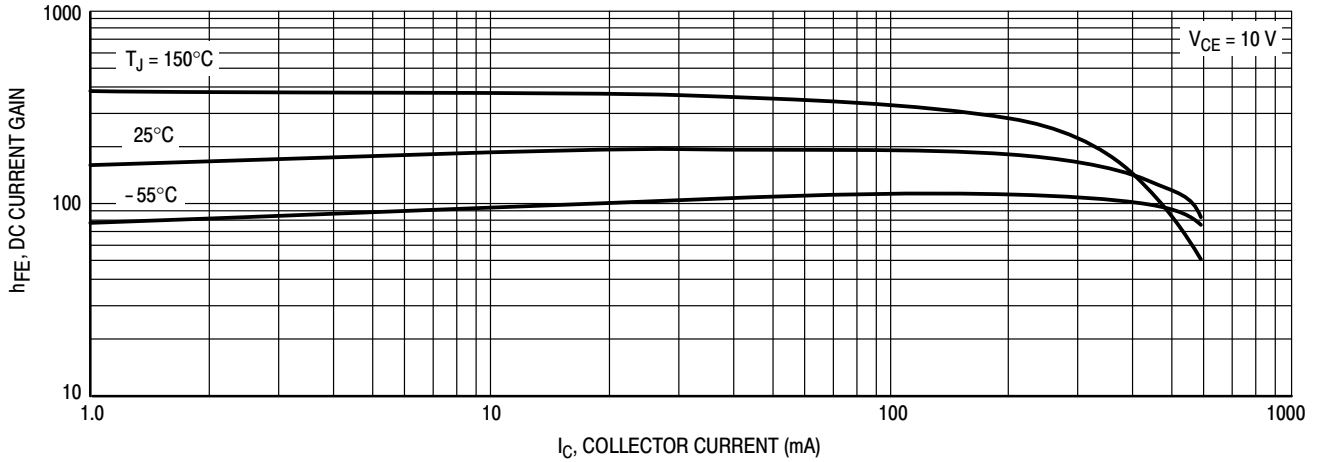


Figure 3. DC Current Gain

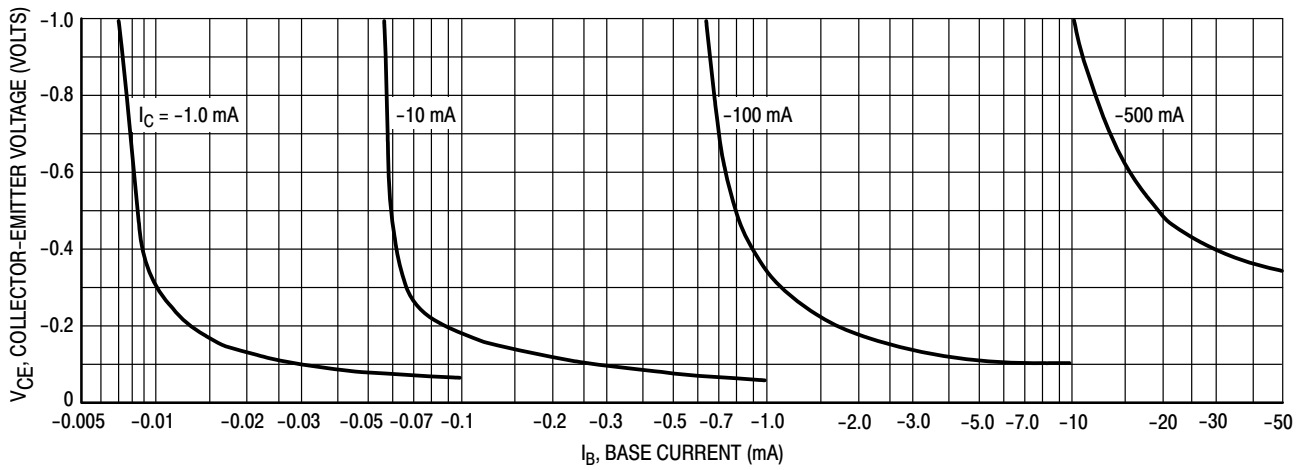


Figure 4. Collector Saturation Region

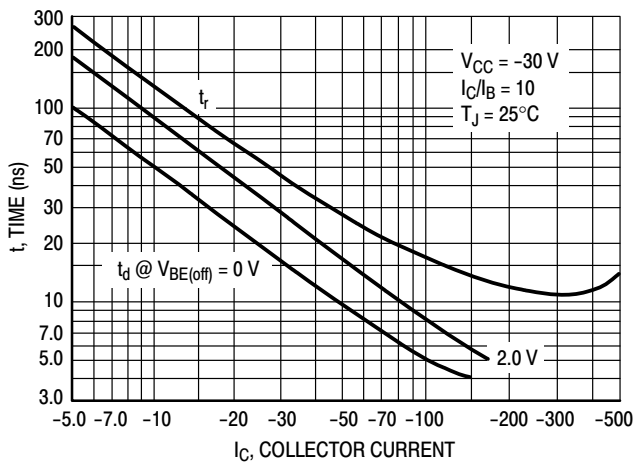


Figure 5. Turn-On Time

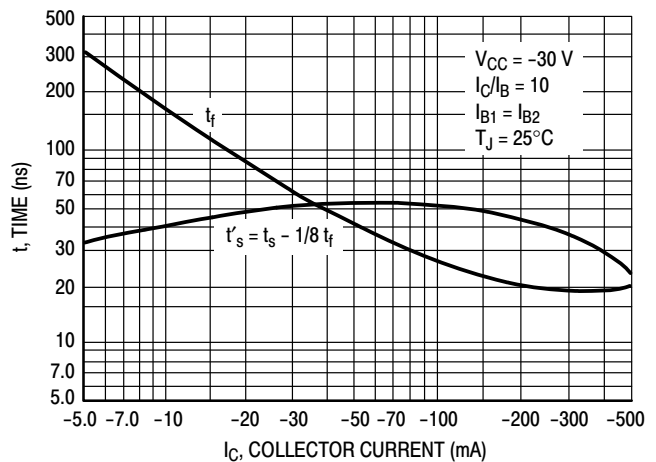


Figure 6. Turn-Off Time

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TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

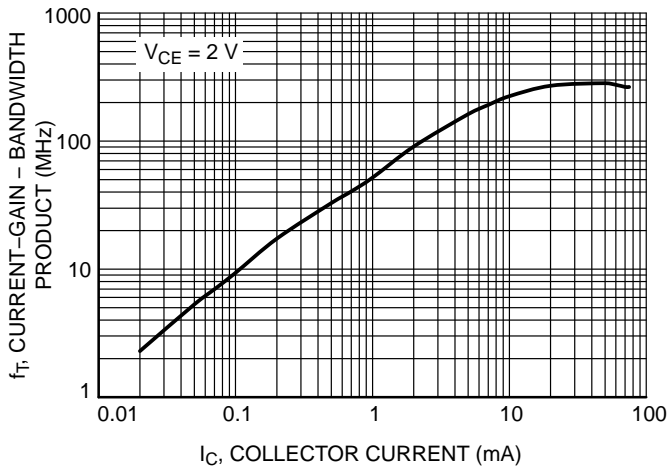


Figure 7. Current-Gain - Bandwidth Product

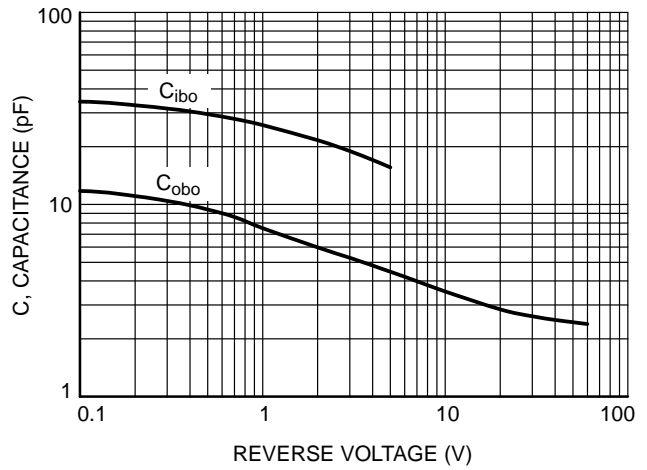


Figure 8. Capacitances

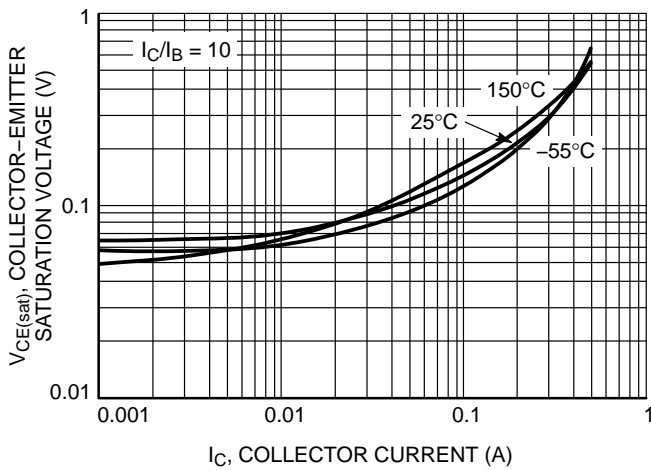


Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

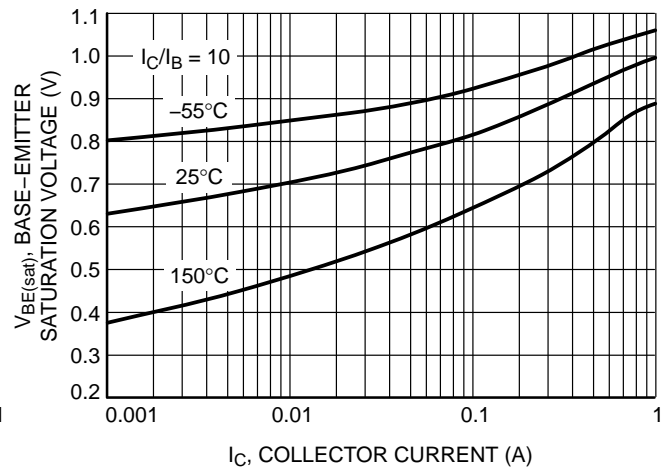


Figure 10. Base Emitter Saturation Voltage vs. Collector Current

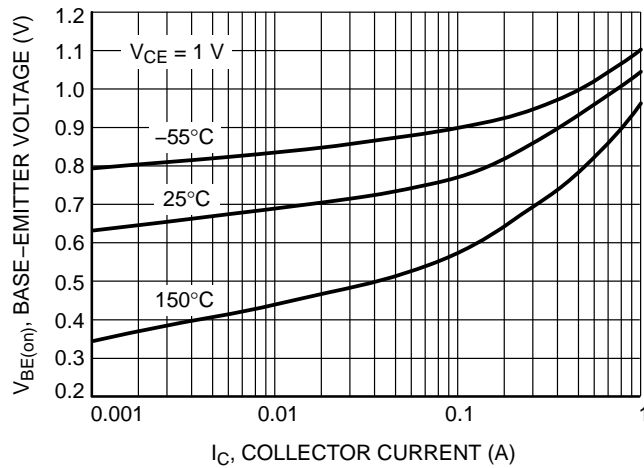
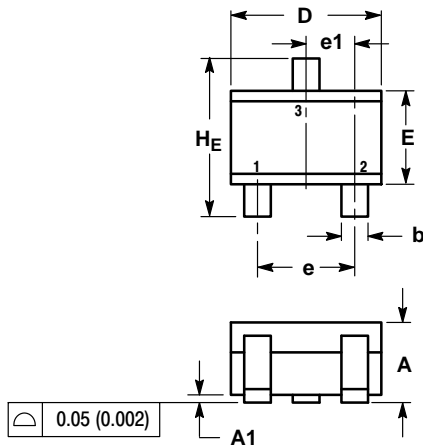


Figure 11. Base Emitter Voltage vs. Collector Current

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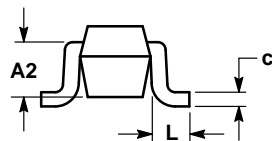
PACKAGE DIMENSIONS

SC-70 (SOT-323)
CASE 419-04
ISSUE N



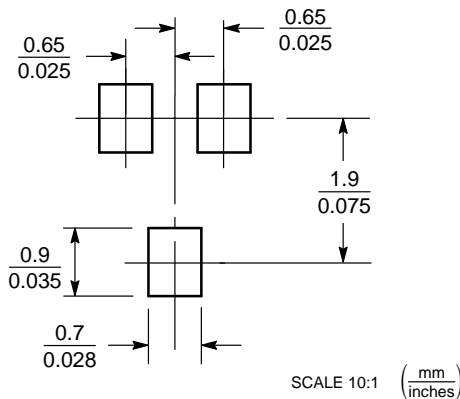
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



- STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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